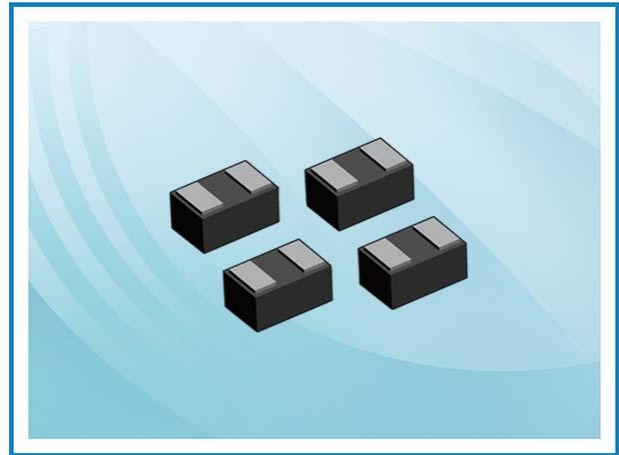


PT0321NS – ESD Protection Diode

Feature

- 48 Watts peak pulse power (8/20 μ s)
- Tiny DFN0603 package
- Bidirectional configurations
- Solid state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Protect one data/power line
- IEC61000-4-2 (ESD) \pm 20kV (Air), \pm 15kV (Contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)
- IEC61000-4-5 (Lightning): 6A (8/20 μ s)



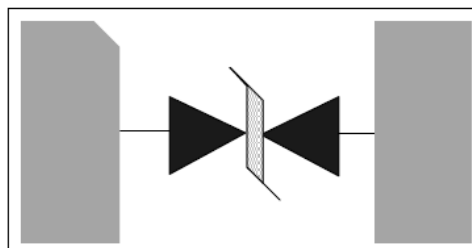
Applications

- Cell Phone Handsets and Accessories
- Micro processor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops and Servers
- Portable Instrumentation

Mechanical Data

- DFN0603 package
- Molding compound flammability rating: UL94 V-0
- Tape and Reel Packaging
- RoHS/WEEE Compliant

Schematic and PIN Configuration



DFN0603

Maximum Rating

Parameter	Symbol	Limit	Unit
IEC61000-4-2 ESD Voltage – Air Mode	$V_{ESD}^{(1)}$	\pm 20	KV
IEC61000-4-2 ESD Voltage – Contact Mode		\pm 15	
Peak Pulse Power	$P_{PP}^{(2)}$	48	W
Peak Pulse Current	$I_{PP}^{(2)}$	6	A
Maximum Lead Solder Temperature (10 seconds duration)	T_L	260	$^{\circ}$ C
Junction Temperature	T_J	-55~125	$^{\circ}$ C
Storage Temperature Range	T_{stg}	-55~125	$^{\circ}$ C

Note:

1. Device stressed with ten non-repetitive ESD pulses.
2. Non-repetitive current pulse 8/20 μ s exponential decay waveform according to IEC61000-4-5.
3. All ratings are measured at environmental temperature of $T_A = 25^{\circ}$ C unless otherwise noted.

PT0321NS – ESD Protection Diode

Electrical Characteristics

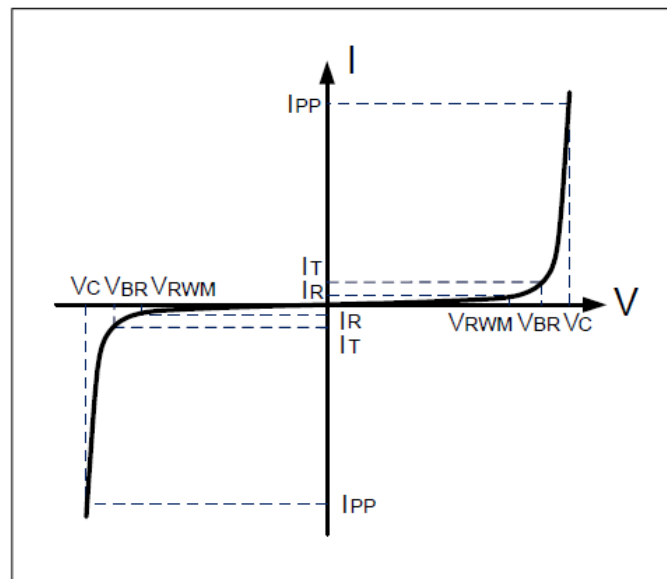
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Stand-off Voltage	$V_{RWM}^{(1)}$				3.3	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1mA$	3.4	4.0		V
Reverse Leakage Current	I_R	$V_{RWM} = 3.3V$			0.2	μA
Peak Pulse Current	I_{PP}				6.0	A
Clamping Voltage ¹⁾	V_{CL}	$I_{PP} = 16A, t_p = 100ns$		8.0		V
Clamping Voltage ²⁾	V_C	$I_{PP} = 1A$		5.0		V
Clamping Voltage ²⁾		$I_{PP} = 6A$		8.0		V
Junction Capacitance	C_J	$V_R = 0V, f = 1MHz$		12		pF

Note:

1. Other voltages available upon request.
2. Non-repetitive current pulse 8/20 μs exponential decay waveform according to IEC61000-4-5.
3. All ratings are measured at environmental temperature of $T_A = 25^\circ C$ unless otherwise noted.

Electrical Parameters

Symbol	Parameter
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Peak Pulse Current
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_R	Reverse Leakage Current @ V_{RWM}
V_{RWM}	Reverse Stand-off Voltage



PT0321NS – ESD Protection Diode

Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

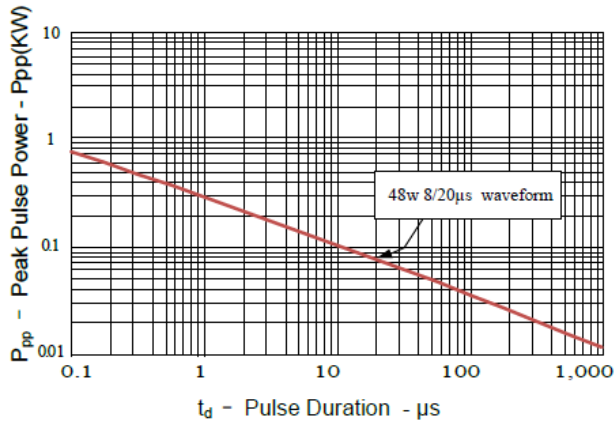


Figure 2: Power Derating Curve

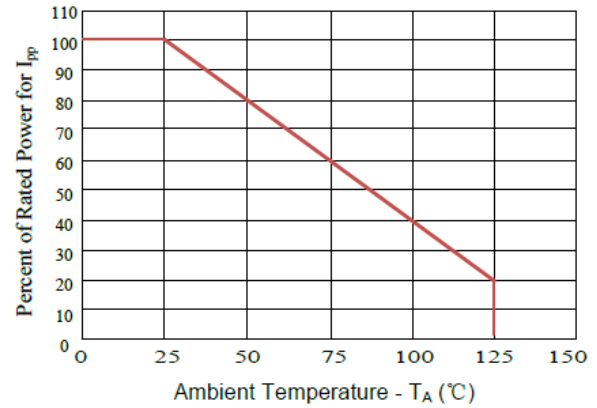


Figure3: Pulse Waveform

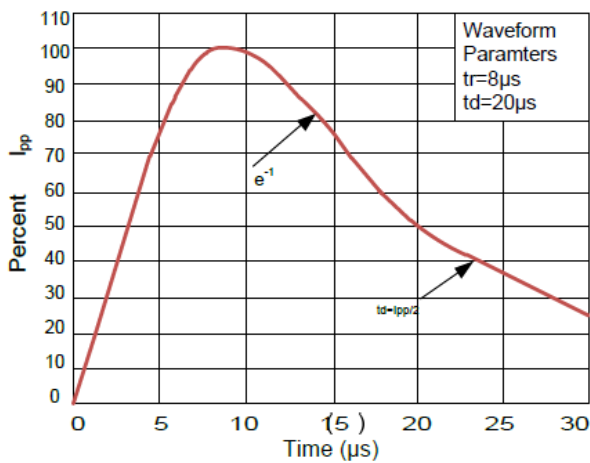
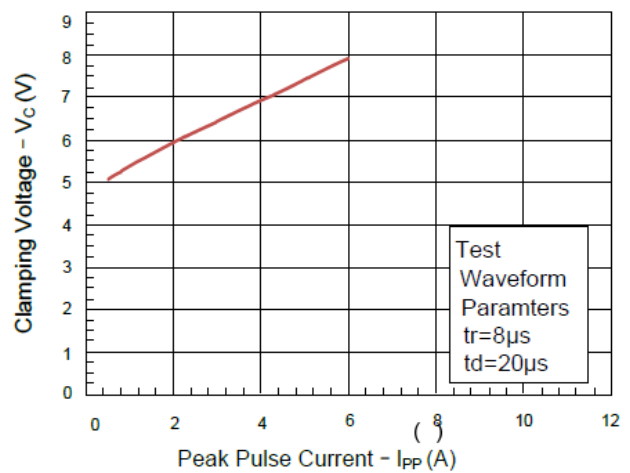
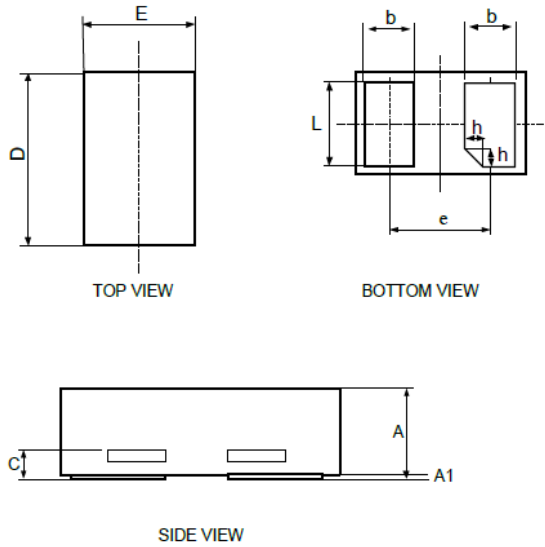


Figure 4: Clamping Voltage vs. Ipp



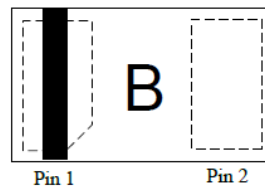
PT0321NS – ESD Protection Diode

DFN0603 Package Outline Dimensions



Symbol	Dimensions (mm)		
	Min	Typ	Max
A	0.28	0.30	0.32
A1	0.00	0.02	0.05
C	0.05	0.10	0.15
D	0.55	0.60	0.65
E	0.25	0.30	0.35
e	0.34	0.35	0.37
b	0.14	0.19	0.24
L	0.20	0.25	0.30
h	0.00	0.05	0.10

Marking



Packaging Information

Order Code	Packaging	Reel Size	PCS/Reel
PT0321NS	DFN0603	7 inch	15,000